N-Channel 200-V (D-S) 175°C MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
200	0.090 @ V_{GS} = 10 V	19
	0.105 @ V_{GS} = 6 V	17.5

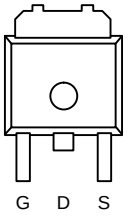
FEATURES

- TrenchFET® Power MOSFET
- 175°C Junction Temperature
- PWM Optimized

APPLICATIONS

- Primary Side Switch

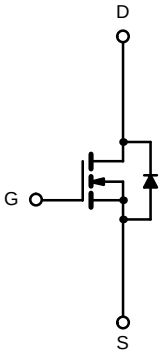
TO-252



Top View

Order Number:
SUD19N20-90

Drain Connected to Tab



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T_A = 25°C UNLESS OTHERWISE NOTED)				
Parameter		**Symbol**	**Limit**	**Unit**
Drain-Source Voltage		V_{DS}	200	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current (T_J = 175°C)[b]	T_C = 25°C	I_D	19	A
	T_C = 125°C		11	
Pulsed Drain Current		I_{DM}	40	
Continuous Source Current (Diode Conduction)		I_S	19	
Avalanche Current		I_{AR}	19	
Repetitive Avalanche Energy (Duty Cycle ≤ 1%)	L = 0.1 mH	E_{AR}	18	mJ
Maximum Power Dissipation	T_C = 25°C	P_D	100[b]	W
	T_A = 25°C		3[a]	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	–55 to 175	°C

THERMAL RESISTANCE RATINGS					
Parameter		**Symbol**	**Typical**	**Maximum**	**Unit**
Junction-to-Ambient[a]	t ≤ 10 sec	R_{thJA}	15	18	°C/W
	Steady State		40	50	
Junction-to-Case (Drain)		R_{thJC}	1.3	1.6	

Notes
a. Surface Mounted on 1" x1" FR4 Board.
b. See SOA curve for voltage derating.

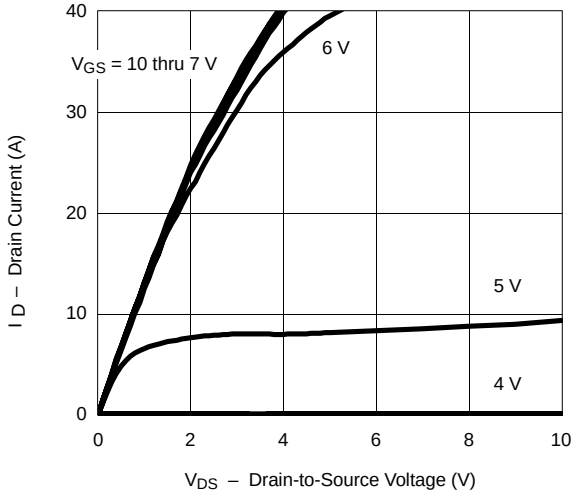
SPECIFICATIONS (T_J = 25°C UNLESS OTHERWISE NOTED)

Parameter	Symbol	Test Condition	Min	Typ[a]	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = 250 μA	200			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 μA	2			
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±20 V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 160 V, V_{GS} = 0 V			1	μA
		V_{DS} = 160 V, V_{GS} = 0 V, T_J = 125°C			50	
		V_{DS} = 160 V, V_{GS} = 0 V, T_J = 175°C			250	
On-State Drain Current[b]	$I_{D(on)}$	V_{DS} = 5 V, V_{GS} = 10 V	40			A
Drain-Source On-State Resistance[b]	$r_{DS(on)}$	V_{GS} = 10 V, I_D = 5 A		0.075	0.090	Ω
		V_{GS} = 10 V, I_D = 5 A, T_J = 125°C			0.190	
		V_{GS} = 10 V, I_D = 5 A, T_J = 175°C			0.260	
		V_{GS} = 6 V, I_D = 5 A		0.082	0.105	
Forward Transconductance[b]	g_{fs}	V_{DS} = 15 V, I_D = 19 A		35		S
Dynamic[a]						
Input Capacitance	C_{iss}	V_{GS} = 0 V, V_{DS} = 25 V, F = 1 MHz		1800		pF
Output Capacitance	C_{oss}			180		
Reverse Transfer Capacitance	C_{rss}			80		
Total Gate Charge[c]	Q_g	V_{DS} = 100 V, V_{GS} = 10 V, I_D = 19 A		34	42	nC
Gate-Source Charge[c]	Q_{gs}			8		
Gate-Drain Charge[c]	Q_{gd}			12		
Turn-On Delay Time[c]	$t_{d(on)}$	V_{DD} = 100 V, R_L = 5.2 Ω I_D ≅ 19 A, V_{GEN} = 10 V, R_G = 2.5 Ω		15	25	ns
Rise Time[c]	t_r			50	75	
Turn-Off Delay Time[c]	$t_{d(off)}$			30	45	
Fall Time[c]	t_f			60	90	
Source-Drain Diode Ratings and Characteristic (T_C = 25°C)						
Pulsed Current	I_{SM}				50	A
Diode Forward Voltage[b]	V_{SD}	I_F = 19 A, V_{GS} = 0 V		0.9	1.5	V
Source-Drain Reverse Recovery Time	t_{rr}	I_F = 19 A, di/dt = 100 A/μs		180	250	ns

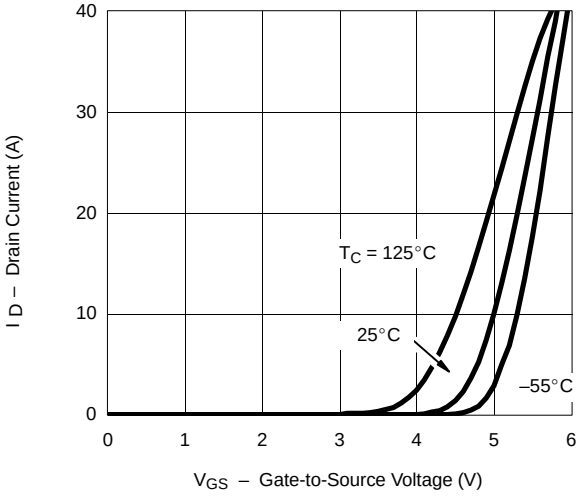
Notes
a. Guaranteed by design, not subject to production testing.
b. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
c. Independent of operating temperature.

TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

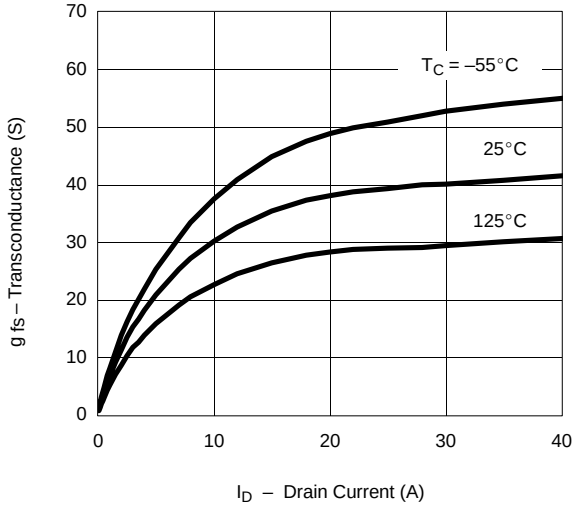
Output Characteristics



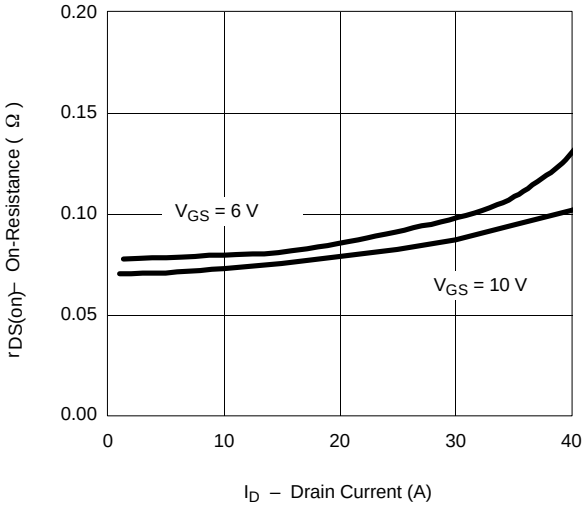
Transfer Characteristics



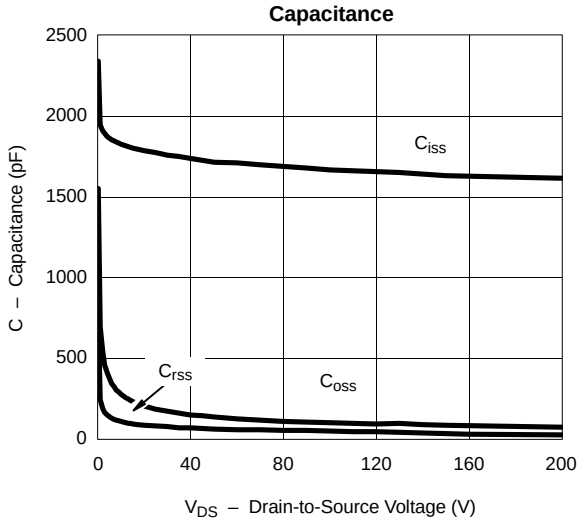
Transconductance



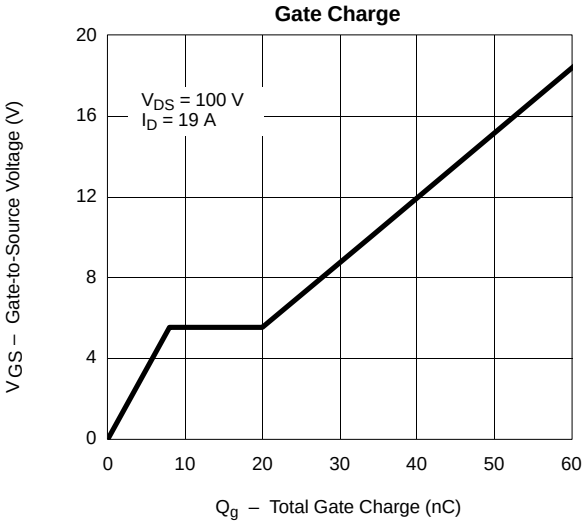
On-Resistance vs. Drain Current



Capacitance

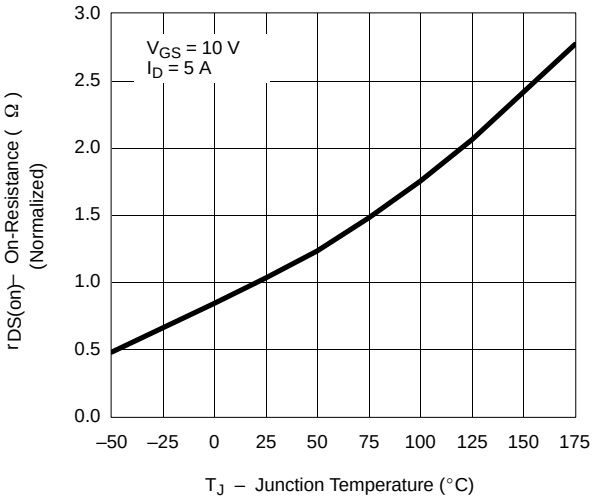


Gate Charge

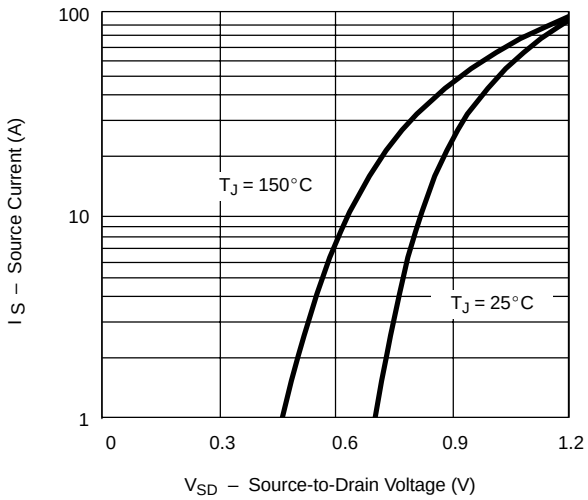


TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

On-Resistance vs. Junction Temperature

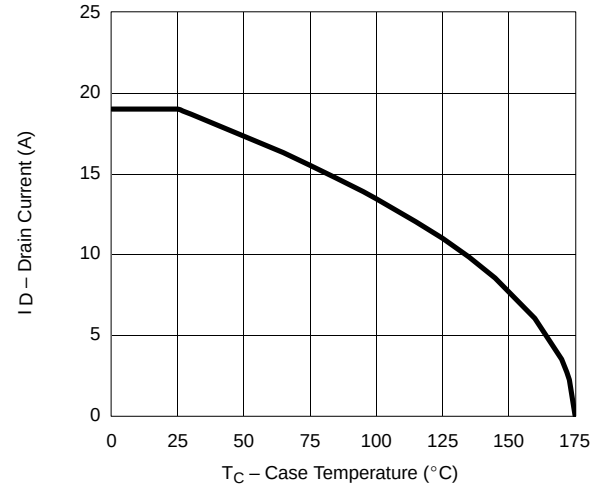


Source-Drain Diode Forward Voltage

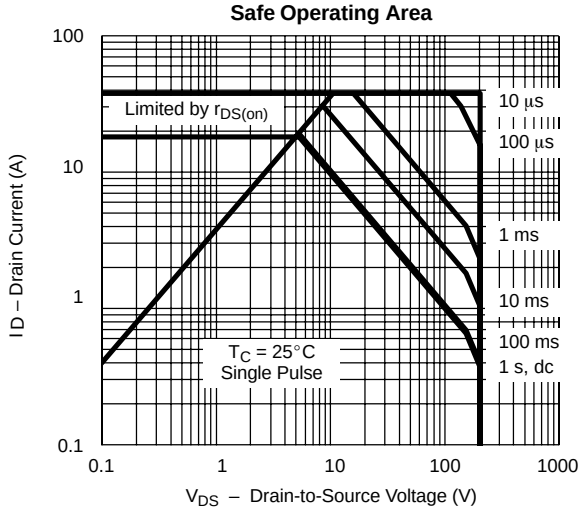


THERMAL RATINGS

Maximum Avalanche Drain Current vs. Case Temperature



Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case